

## REMARKS

Claims 8 and 9 have been amended. Claims 8 and 9 are presently active in the subject application.

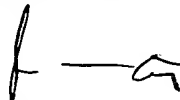
Claims 8 and 9 were rejected under 35 U.S.C. 103(a) as being unpatentable over Arai (U.S. 5,841,174) in view of Watabe et al.(4,727,038). The rejection is respectfully traversed.

(a) [forming] a gate dielectric over a semiconductor region;

Claims 8 and 9 require that there be a unitary electrically conductive metallic material entirely covering said gate. This is particularly shown in connection with Fig. 2D, wherein the wrap-around silicidation of the polysilicon gate is shown. This structure results from the conformal deposition of a metal to be silicided over the entire exposed gate structure as shown in Fig. 2C. The existence of this type of structure is important as stated in the specification at page 8, lines 9 to 11 where it is stated "the conformal metal on the sidewalls of the gate acts to mask that portion of the substrate from receiving this implant". Accordingly, the sidewall metallization performs a dual purpose which could have required additional processing in accordance with the prior art. No such structure is taught or suggested by the cited references taken alone or in any proper combination.

In view of the above remarks, favorable reconsideration and allowance are respectfully requested.

Respectfully submitted,



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